

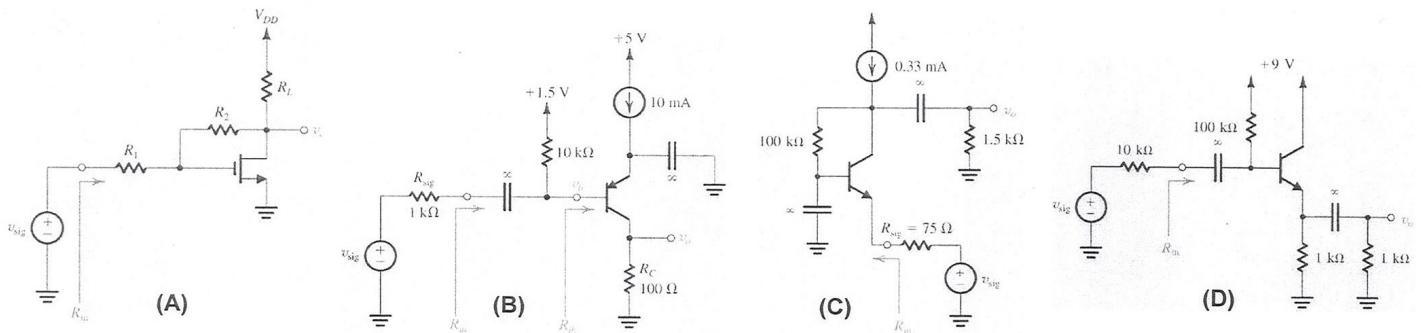
國立中央大學九十九學年度電機系碩士在職專班招生試題

筆試科目：基礎電子學

考試時間：100 分鐘

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- 選擇題 (7 分)** 對一互補式金氧半電晶體反相器(CMOS inverter)而言，下列何者敘述有誤？(A)由 NMOSFET 與 PMOSFET 共同組成，(B)功率損耗較 NMOS inverter 大，(C) noise margin 較 NMOS inverter 大，(D)以上皆非。
- 選擇題 (7 分)** 對一金氧半電晶體(MOSFET)而言，下列何者敘述為真？(A)為一四端點(four terminals)元件，(B) enhancement-mode PMOSFET 之臨限電壓(threshold voltage, V_t)小於 0 V，(C)在相同的元件結構與幾何大小下，NMOSFET 之電流高於 PMOSFET (D)以上皆真。
- 選擇題 (7 分)** 下列何種電路屬於 BJT 共集極態？



- 計算題 (24 分)** The NMOS transistors in Fig. 1 have $V_t = 1$ V, $\mu_n C_{ox} = 120 \mu\text{A/V}^2$, $\lambda = 0$ (or $V_A = \infty$), and $L_1 = L_2 = 1 \mu\text{m}$. Find the required values of gate width for each of Q_1 and Q_2 to obtain the voltage and current values indicated.

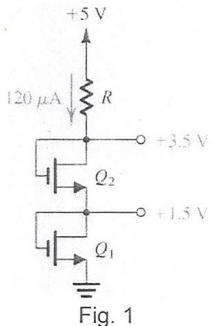


Fig. 1

Operation	NMOSFETs	PMOSFETs
Saturation	$I_d = k_n(V_{GS}-V_t)^2$	$I_d = k_p(V_{SG}+V_t)^2$
Triode	$I_{dn} = k_n[2(V_{GS}-V_t)V_{DS}-V_{DS}^2]$	$I_{dp} = k_p[2(V_{SG}+V_t)V_{SD}-V_{SD}^2]$
Transition Point	$V_{DS(sat)} = V_{GS}-V_t$	$V_{SD(sat)} = V_{SG}+V_t$
	$k_n = W\mu_n C_{ox}/2L$	$k_p = W\mu_p C_{ox}/2L$
Small signal parameters:	$g_m = 2\sqrt{k_n I_{DQ}}$, $r_o = V_A/I_{DQ}$	

- 計算題 (25 分)** Figure 2 shows an ideal op-amp.

5-1 (16 分) Find I_1 , I_2 , I_3 , and V_x .

5-2 (9 分) If V_O is not to be lower than -13 V, find the maximum allowed value for R_L .

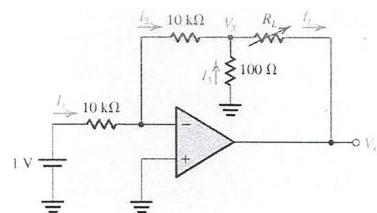


Fig. 2

- 計算題 (10 分)** For the current steering circuit of Fig. 3, find I_O in terms of I_{REF} and device (W/L) ratios, such as $(W/L)_1$, $(W/L)_2$, $(W/L)_3$, and $(W/L)_4$.

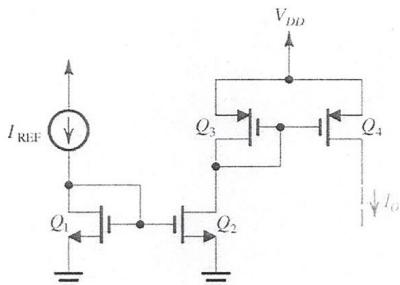


Fig. 3

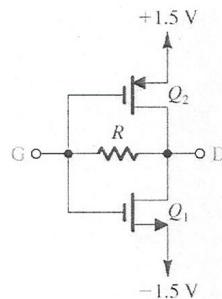


Fig. 4

- 計算題 (20 分)** The MOSFETs in the buffer amplifier shown in Fig. 4 are matched, having $\mu_n C_{ox} (W/L)_1 = \mu_p C_{ox} (W/L)_2 = 1 \text{ mA/V}^2$ and $|V_t| = 0.5$ V. The resistance $R = 1 \text{ M}\Omega$.

7-1 (10 分) For G and D open, find the values of drain currents I_{D1} and I_{D2} .

7-2 (10 分) For infinite r_o , find the voltage gain of the amplifier from G to D.